

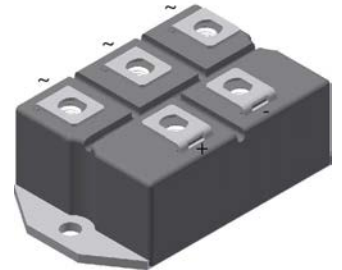
Standard Rectifier Module

3~ Rectifier	
$V_{RRM} =$	1200 V
$I_{DAV} =$	60 A
$I_{FSM} =$	550 A

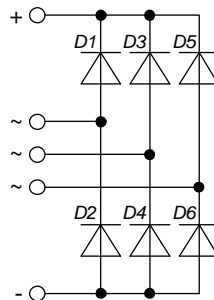
3~ Rectifier Bridge

Part number

VUO62-12N07



 E72873



Features / Advantages:

- Package with DCB ceramic
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- Diode for main rectification
- For three phase bridge configurations
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Package: PWS-D

- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Easy to mount with two screws
- Base plate: Copper internally DCB isolated
- Advanced power cycling

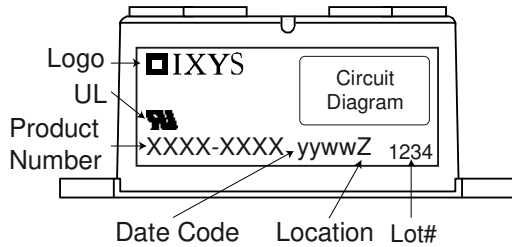
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Rectifier				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V_{RSM}	max. non-repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1300	V	
V_{RRM}	max. repetitive reverse blocking voltage	$T_{VJ} = 25^{\circ}C$			1200	V	
I_R	reverse current	$V_R = 1200\text{ V}$	$T_{VJ} = 25^{\circ}C$		40	μA	
		$V_R = 1200\text{ V}$	$T_{VJ} = 150^{\circ}C$		1,5	mA	
V_F	forward voltage drop	$I_F = 20\text{ A}$	$T_{VJ} = 25^{\circ}C$		1,07	V	
		$I_F = 60\text{ A}$			1,30	V	
		$I_F = 20\text{ A}$	$T_{VJ} = 125^{\circ}C$		0,96	V	
		$I_F = 60\text{ A}$			1,27	V	
I_{DAV}	bridge output current	$T_C = 120^{\circ}C$ rectangular $d = \frac{1}{3}$	$T_{VJ} = 150^{\circ}C$		60	A	
V_{FO}	threshold voltage	} for power loss calculation only	$T_{VJ} = 150^{\circ}C$		0,78	V	
r_F	slope resistance				8,1	m Ω	
R_{thJC}	thermal resistance junction to case				1,1	K/W	
R_{thCH}	thermal resistance case to heatsink			0,4		K/W	
P_{tot}	total power dissipation		$T_C = 25^{\circ}C$		110	W	
I_{FSM}	max. forward surge current	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}C$		550	A	
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$		595	A	
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}C$		470	A	
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$		505	A	
I^2t	value for fusing	$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 45^{\circ}C$		1,52	kA ² s	
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$		1,48	kA ² s	
		$t = 10\text{ ms; (50 Hz), sine}$	$T_{VJ} = 150^{\circ}C$		1,11	kA ² s	
		$t = 8,3\text{ ms; (60 Hz), sine}$	$V_R = 0\text{ V}$		1,06	kA ² s	
C_J	junction capacitance	$V_R = 400\text{ V; } f = 1\text{ MHz}$	$T_{VJ} = 25^{\circ}C$		19	pF	



Package PWS-D		Ratings				
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			150	A
T_{VJ}	virtual junction temperature		-40		150	°C
T_{op}	operation temperature		-40		125	°C
T_{stg}	storage temperature		-40		125	°C
Weight				159		g
M_D	mounting torque		4,25		5,75	Nm
M_T	terminal torque		4,25		5,75	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	9,5			mm
$d_{Spb/Apb}$		terminal to backside	26,0			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V

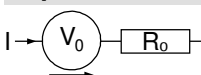


Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VUO62-12NO7	VUO62-12NO7	Box	10	460451

Equivalent Circuits for Simulation

* on die level

$T_{VJ} = 150^{\circ}C$

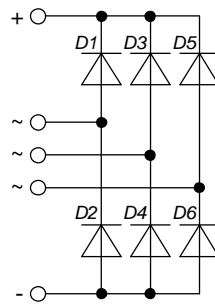
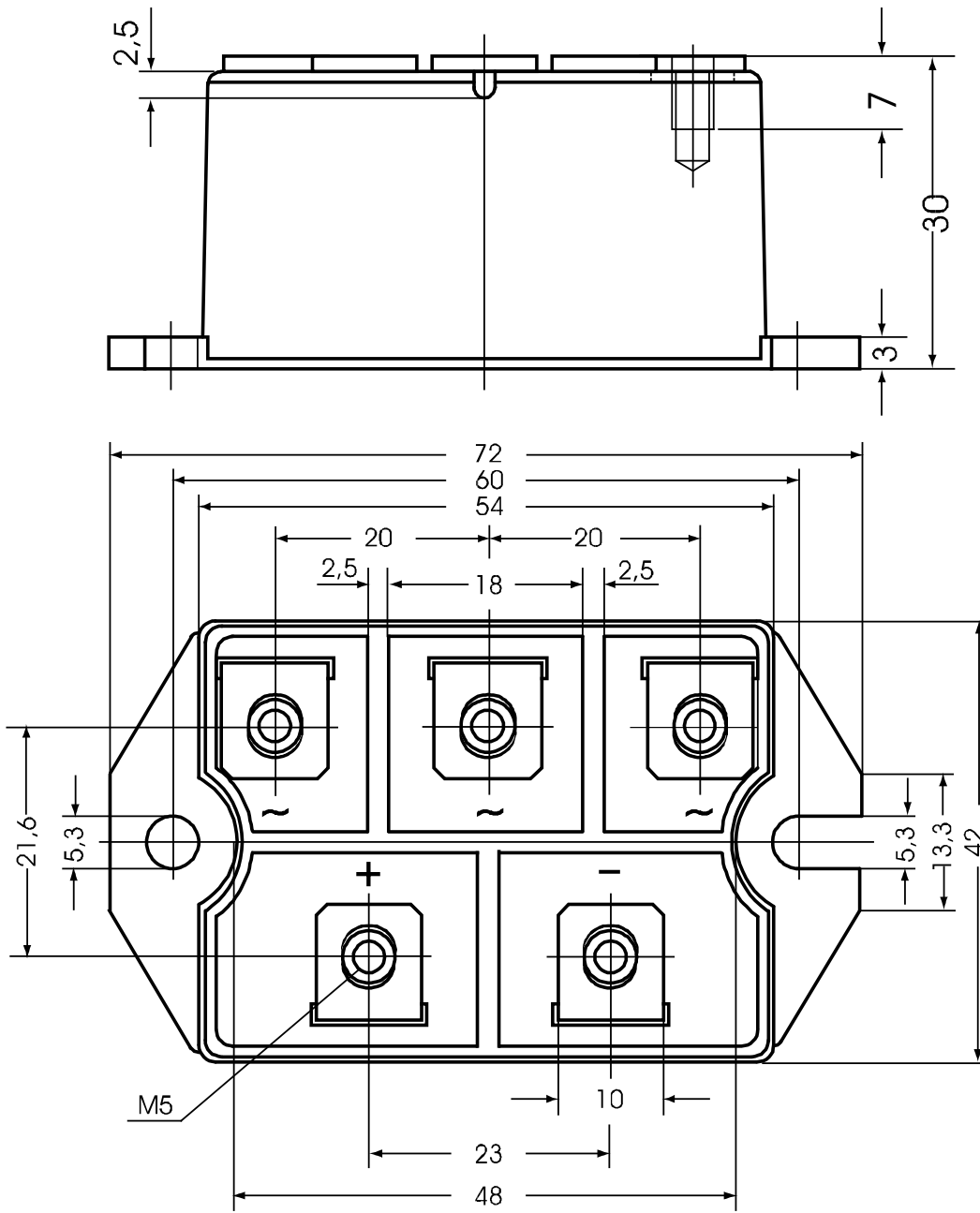


Rectifier

$V_{0\ max}$	threshold voltage	0,78	V
$R_{0\ max}$	slope resistance *	6,9	mΩ



Outlines PWS-D





Rectifier

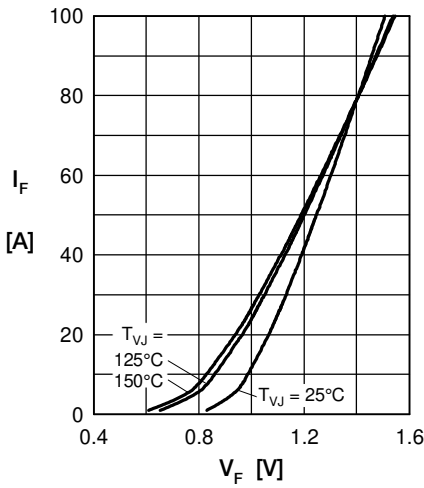


Fig. 1 Forward current vs. voltage drop per diode

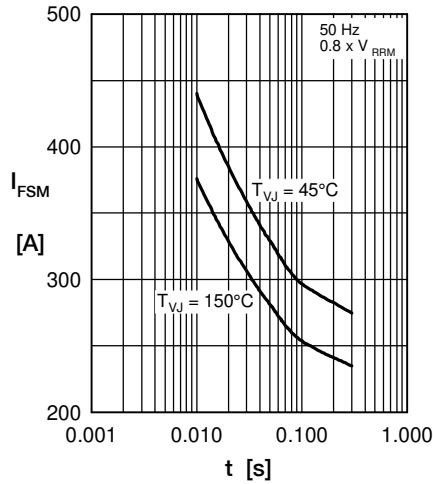


Fig. 2 Surge overload current vs. time per diode

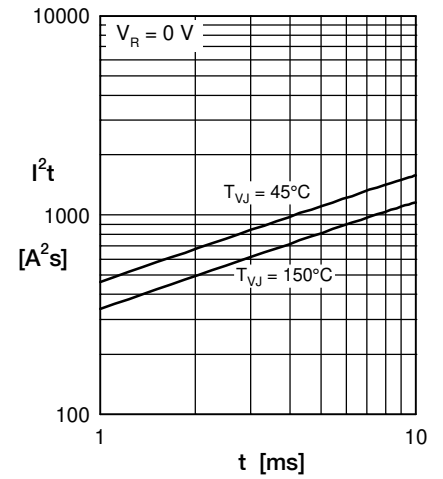


Fig. 3 I^2t vs. time per diode

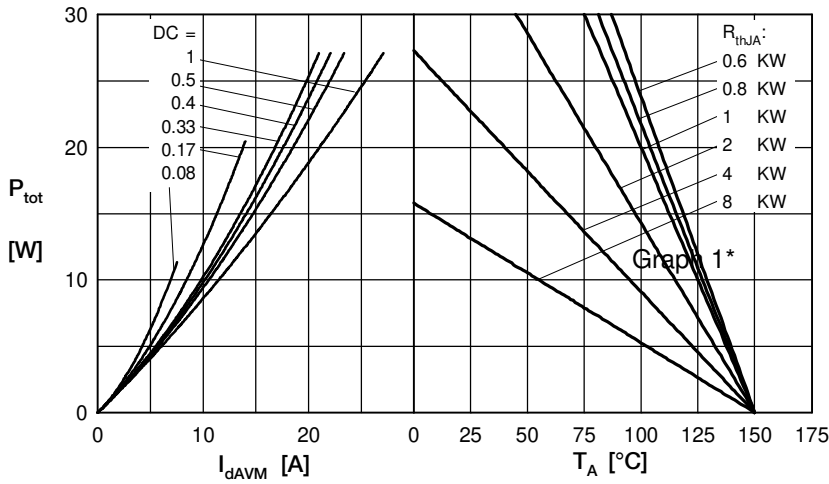


Fig. 4 Power dissipation vs. forward current and ambient temperature per diode

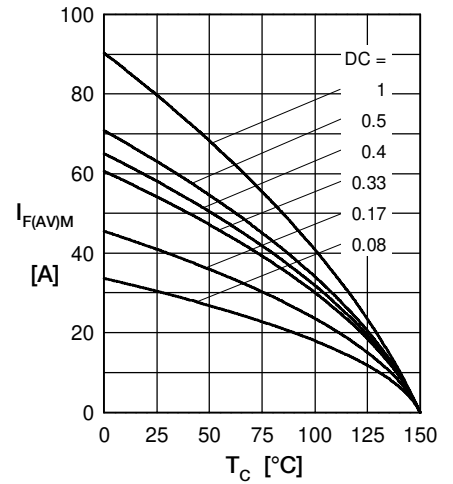


Fig. 5 Max. forward current vs. case temperature per diode

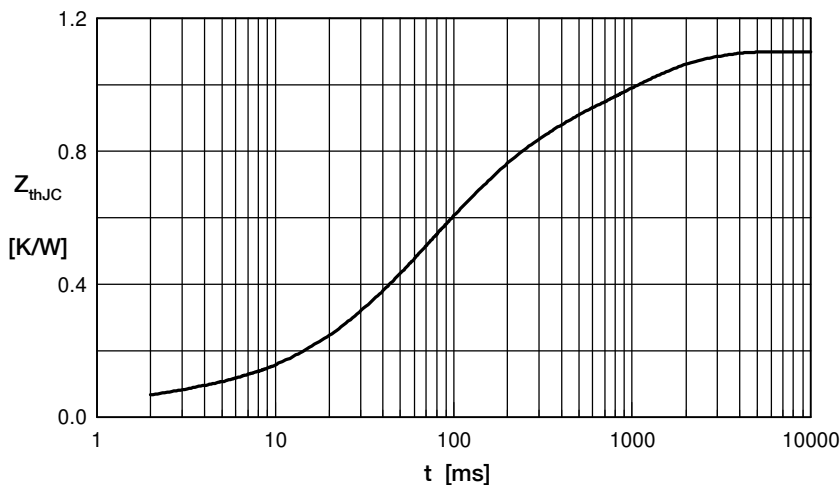


Fig. 6 Transient thermal impedance junction to case vs. time per diode

Constants for Z_{thJC} calculation:

i	R_{th} (K/W)	t_i (s)
1	0.05	0.001
2	0.14	0.030
3	0.25	0.060
4	0.35	0.130
5	0.31	0.920